

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLX15** is a Common Emitter Device Designed for High Linearity Class A/AB HF Applications.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	10 A
V_{CB}	110 V
P_{DISS}	233 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
θ_{JC}	0.75 °C/W

PACKAGE STYLE .550 4L STUD

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5.59	.230/5.84
B		1.050/26.67
C	.545/13.84	.555/14.10
D	.495/12.57	.505/12.83
E	.003/0.08	.007/0.18
F		.830/21.08
G	.185/4.70	.198/5.03
H	.497/12.62	.530/13.46

1 = COLLECTOR 2 & 4 = EMITTER
3 = BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 100 mA	55			V
BV_{CBO}	I _C = 100 mA	110			V
BV_{EBO}	I _E = 10 mA	4.0			V
h_{FE}	V _{CE} = 6.0 V I _C = 1.4 A	15		50	---
P_g	V _{CE} = 50 V I _{cq} = 100 mA	14	---	---	dB
IMD₃	P _{out} = 150 W(PEP) f = 30 MHz	---	-37	-30	dBc
η_C		37	45	---	%
C_{ob}	V _{CB} = 50 V f = 1.0 MHz			220	pF